

Hexfred Die in Wafer Form

1200 V
Size 50
5" Wafer

Electrical Characteristics (Wafer Form)

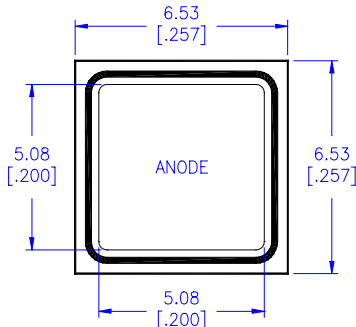
Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V_{FM}	Forward Voltage	3.0V Max.	$T_J = 25^{\circ}\text{C}$, $I_F = 16\text{A}$
BV_R	Reverse Breakdown Voltage	1200V Min.	$T_J = 25^{\circ}\text{C}$, $I_R = 200\mu\text{A}$
I_{RM}	Reverse Leakage Current	20 μA Max.	$T_J = 25^{\circ}\text{C}$, $V_R = 1200\text{V}$

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr-Ni-Ag (1kA-4kA-6kA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.257" x 0.257"
Wafer Diameter	125mm, with std. < 100 > flat
Wafer Thickness	.015" $\pm$.003"
Relevant Die Mechanical Dwg. Number	01-5168
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Recommended Storage Environment	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) :HFA30PB120

Die Outline



NOTES:

- ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES)
- CONTROLLING DIMENSION : (INCH)
- DIMENSIONAL TOLERANCES:
 BONDING PADS : < 0.635 TOLERANCE = ± 0.013
 WIDTH < (.0250) TOLERANCE = $\pm (.0005)$
 & > 0.635 TOLERANCE = ± 0.025
 LENGTH > (.0250) TOLERANCE = $\pm (.0010)$
 OVERALLDIE < 1.270 TOLERANCE = ± 0.102
 WIDTH < (.050) TOLERANCE = $\pm (.004)$
 & > 1.270 TOLERANCE = ± 0.203
 LENGTH > (.050) TOLERANCE = $\pm (.008)$